DOSEMI

IGBT

DG75A08TAFS

750V/75A IGBT with Diode

General Description

DOSEMI IGBT Power Discrete provides ultra low conduction loss as well as low switching loss. They are designed for the applications such as solar power.

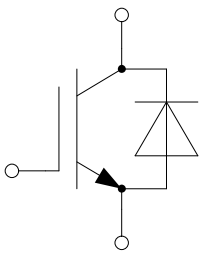
Features

- Low $V_{CE(sat)}$ Fast IGBT technology
- Low switching loss
- Maximum junction temperature 175°C
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD

Typical Applications

- Solar power
- UPS
- 3-level-application

Equivalent Circuit Schematic



Type	Package	Marking	Shipping
DG75A08TAFS	TO-247-3L	DG75A08TAFS	30Units/Tube

Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	750	V
V_{GES}	Gate-Emitter Voltage Transient Gate-Emitter Voltage	±20 ±30	V
I_C	Collector Current @ T_C=25°C @ T_C=90°C	100 75	A
I_{CRM}	Repetitive Peak Collector Current tp limited by T_{vjop}	225	A
P_D	Maximum Power Dissipation @ T_{vj}=175°C	340	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	750	V
I_F	Diode Continuous Forward Current @ T_C=25°C @ T_C=100°C	100 75	A
I_{FRM}	Repetitive Peak Forward Current tp limited by T_{vjop}	225	A

Discrete

Symbol	Description	Values	Unit
T_{vjop}	Operating Junction Temperature	-40 to +175	°C
T_{STG}	Storage Temperature Range	-55 to +150	°C
T_S	Soldering Temperature,1.6mm from case for 10s	260	°C
M	Mounting Torque, Screw M3	0.6	N.m

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=75A,V_{GE}=15V, T_{vj}=25°C		1.65	2.10	V
		I_C=75A,V_{GE}=15V, T_{vj}=150°C		2.05		
		I_C=75A,V_{GE}=15V, T_{vj}=175°C		2.10		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=1.5mA,V_{CE}=V_{GE}, T_{vj}=25°C	3.5	4.0	4.5	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_{vj}=25°C			200	uA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_{vj}=25°C			100	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	V_{CE}=25V,f=100kHz, V_{GE}=0V		2.80		nF
C_{oes}	Output Capacitance			0.22		nF
C_{res}	Reverse Transfer Capacitance			0.02		nF
Q_G	Gate Charge	V_{GE}=-15…+15V		0.17		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=400V,I_C=75A, R_G=7.5Ω,L_S=40nH, V_{GE}=±15V,T_{vj}=25 °C		36		ns
t_r	Rise Time			76		ns
$t_{d(off)}$	Turn-Off Delay Time			94		ns
t_f	Fall Time			20		ns
E_{on}	Turn-On Switching Loss			3.38		mJ
E_{off}	Turn-Off Switching Loss			1.06		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=400V,I_C=75A, R_G=7.5Ω,L_S=40nH, V_{GE}=±15V,T_{vj}=150 °C		40		ns
t_r	Rise Time			77		ns
$t_{d(off)}$	Turn-Off Delay Time			114		ns
t_f	Fall Time			28		ns
E_{on}	Turn-On Switching Loss			4.59		mJ
E_{off}	Turn-Off Switching Loss			1.53		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=400V,I_C=75A, R_G=7.5Ω,L_S=40nH, V_{GE}=±15V,T_{vj}=175 °C		40		ns
t_r	Rise Time			77		ns
$t_{d(off)}$	Turn-Off Delay Time			118		ns
t_f	Fall Time			32		ns
E_{on}	Turn-On Switching Loss			4.96		mJ
E_{off}	Turn-Off Switching Loss			1.61		mJ

Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_C=75A,V_{GE}=0V,T_{vj}=25°C		1.55	2.00	V
		I_C=75A,V_{GE}=0V,T_{vj}=150°C		1.50		
		I_C=75A,V_{GE}=0V,T_{vj}=175°C		1.45		
t_{rr}	Diode Reverse Recovery Time	V_R=400V,I_F=75A, -di/dt=780A/µs,Ls=40nH, V_{GE}=-15V,T_{vj}=25°C		120		ns
Q_r	Recovered Charge			2.74		µC
I_{RM}	Peak Reverse Recovery Current			33		A
E_{rec}	Reverse Recovery Energy			0.66		mJ
t_{rr}	Diode Reverse Recovery Time	V_R=400V,I_F=75A, -di/dt=710A/µs,Ls=40nH, V_{GE}=-15V,T_{vj}=150°C		198		ns
Q_r	Recovered Charge			5.72		µC
I_{RM}	Peak Reverse Recovery Current			47		A
E_{rec}	Reverse Recovery Energy			1.35		mJ
t_{rr}	Diode Reverse Recovery Time	V_R=400V,I_F=75A, -di/dt=690A/µs,Ls=40nH, V_{GE}=-15V,T_{vj}=175°C		215		ns
Q_r	Recovered Charge			6.55		µC
I_{RM}	Peak Reverse Recovery Current			50		A
E_{rec}	Reverse Recovery Energy			1.56		mJ

Discrete Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.440 0.417	K/W
R_{thJA}	Junction-to-Ambient		40		K/W

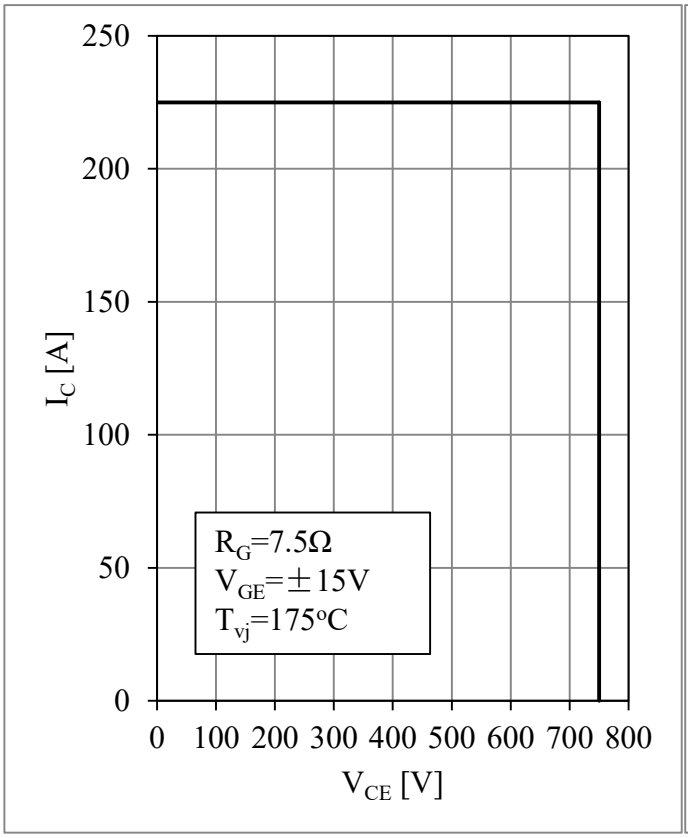


Fig 1. RBSOA

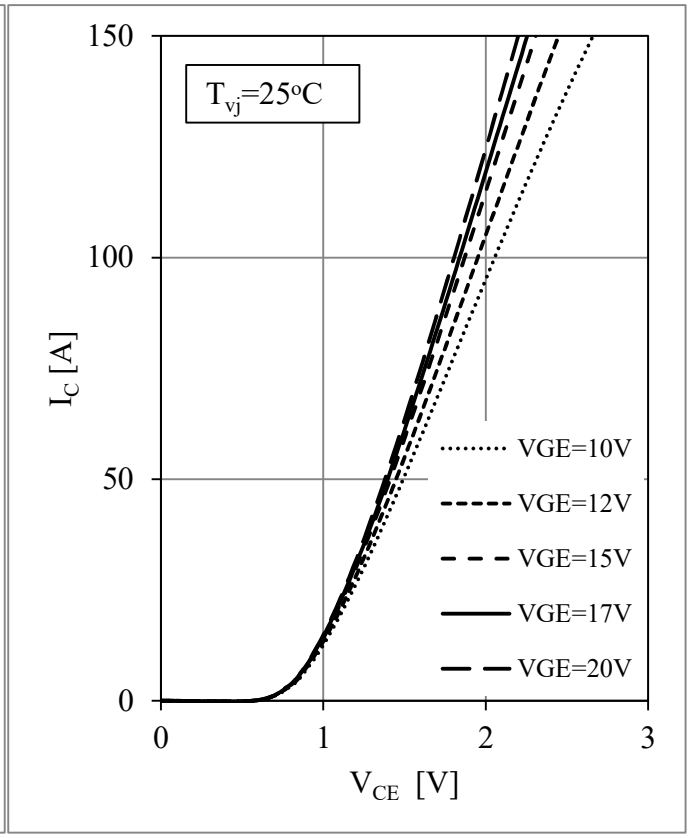


Fig 2. IGBT Output Characteristics

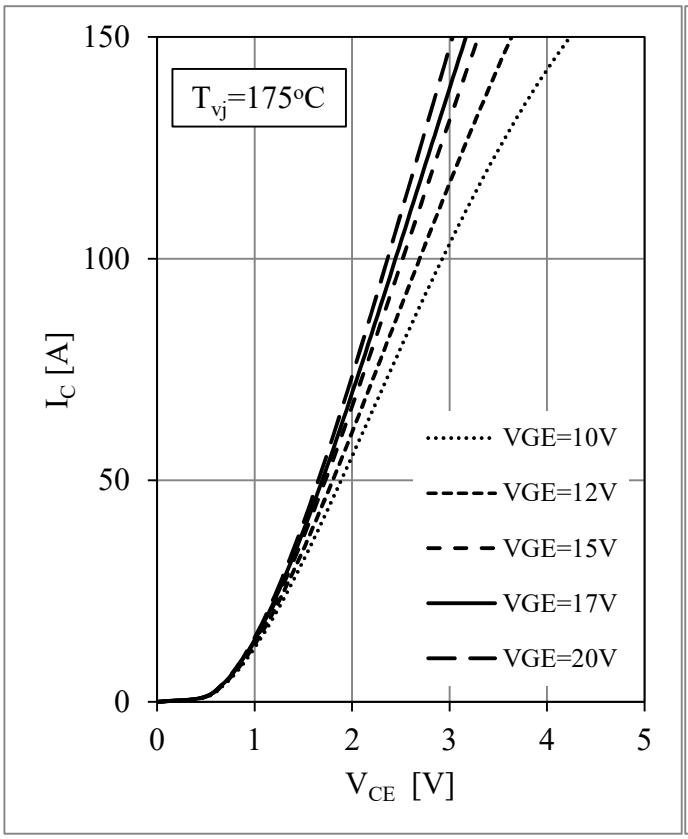


Fig 3. IGBT Output Characteristics

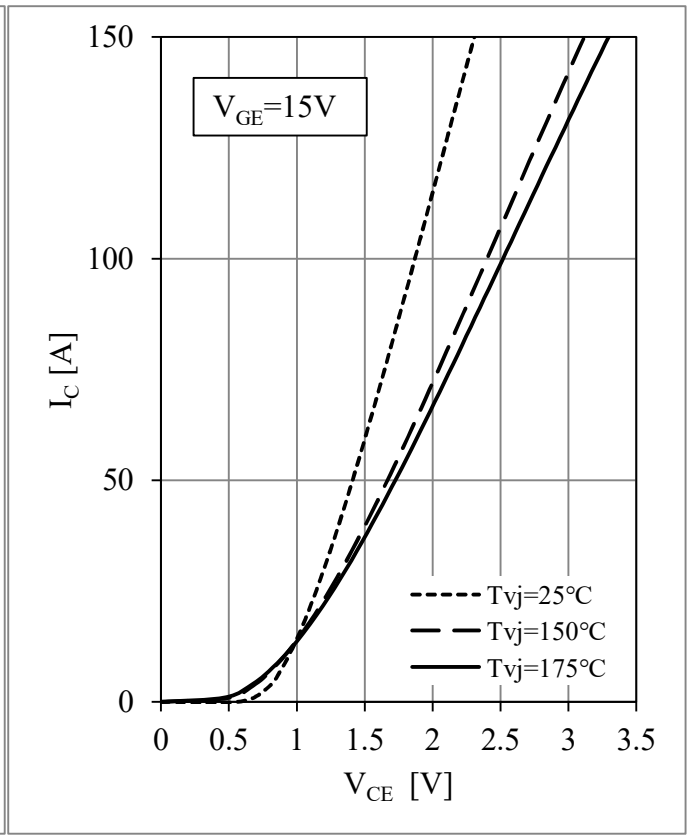


Fig 4. IGBT Output Characteristics

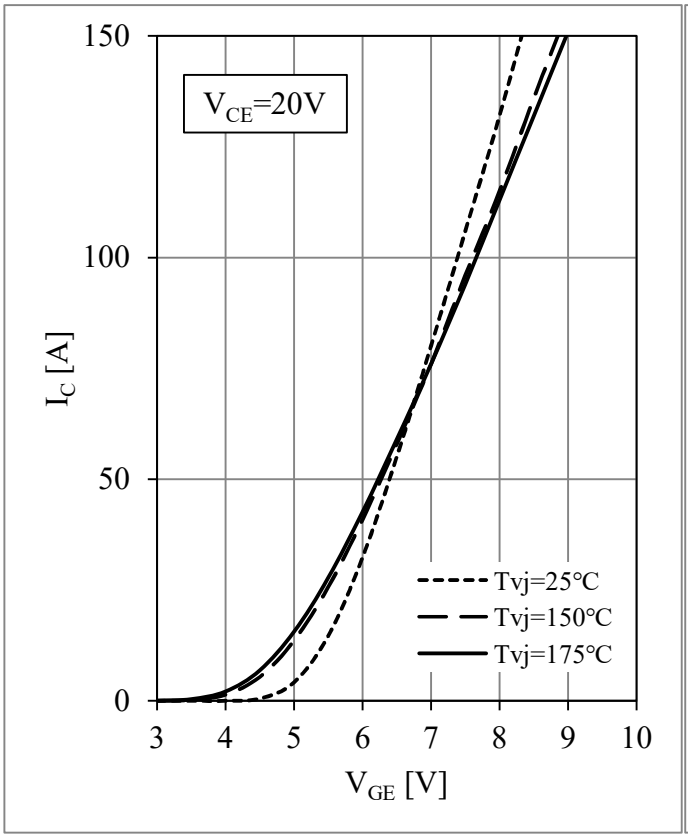


Fig 5. IGBT Transfer Characteristics

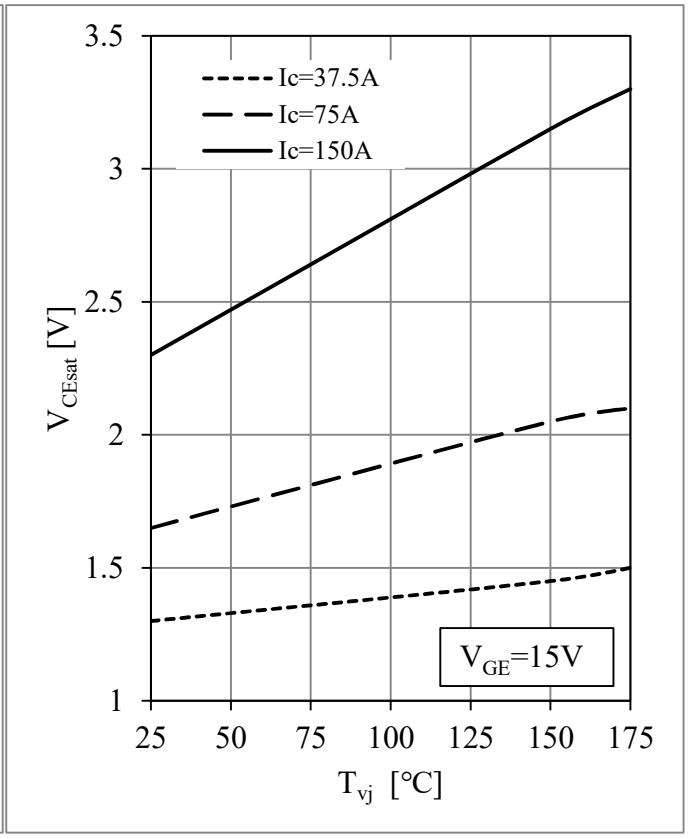


Fig 6. Collector-emitter saturation voltage vs T_{vj}

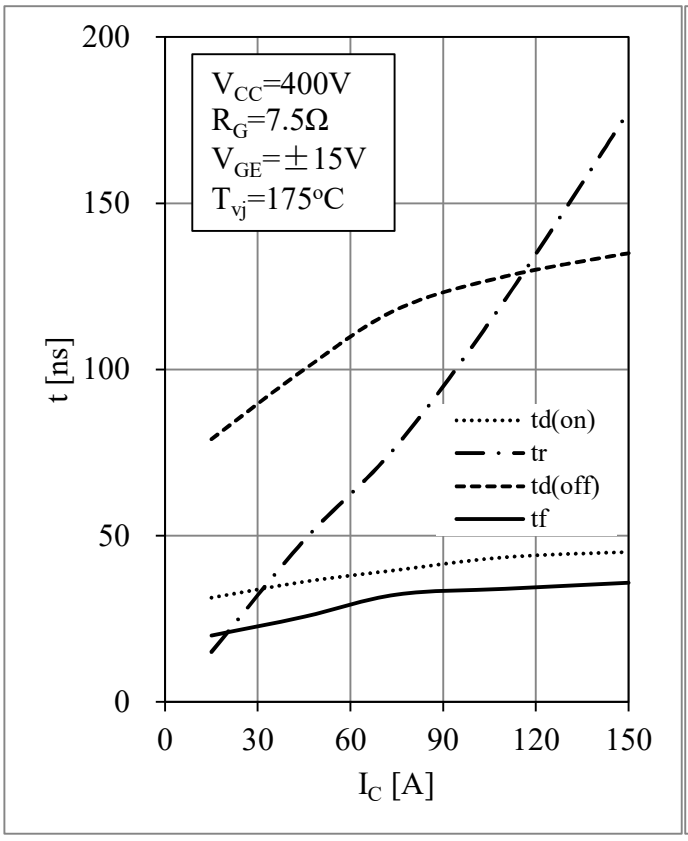


Fig 7. IGBT Switching Times as. Ic

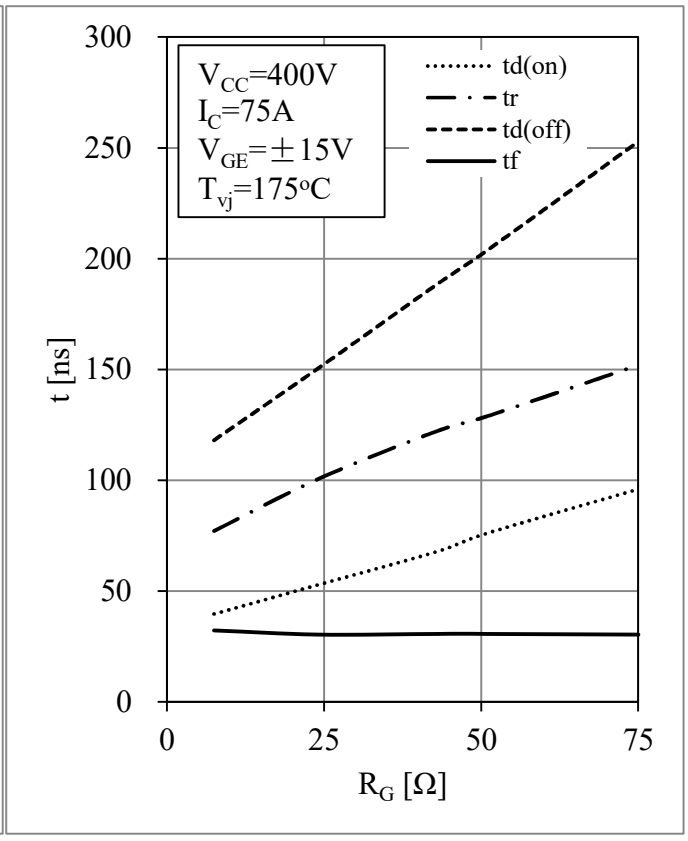


Fig 8. IGBT Switching Times as.R_G

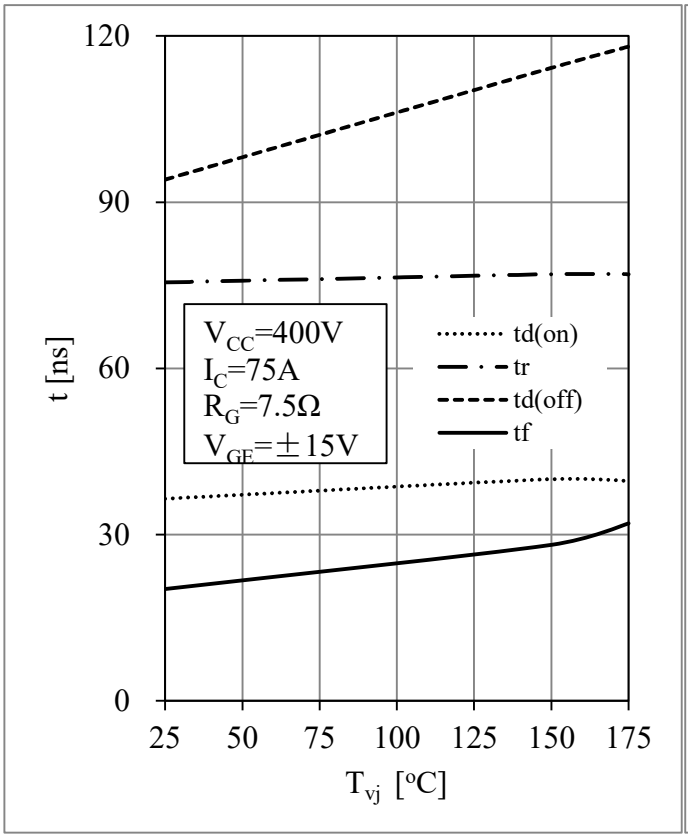


Fig 9. IGBT Switching Times as. T_{vj}

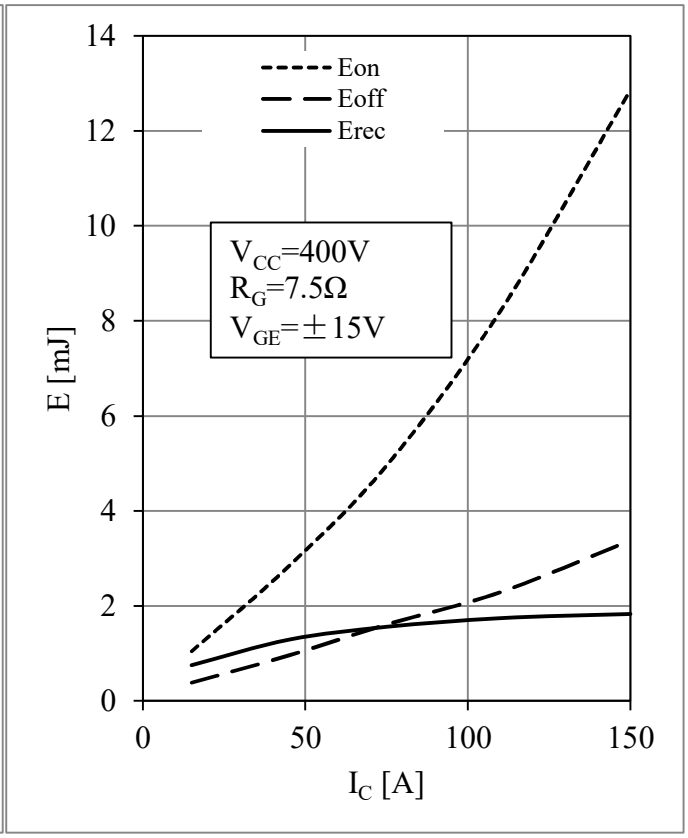


Fig 10. Switching Energy Loss vs. I_C

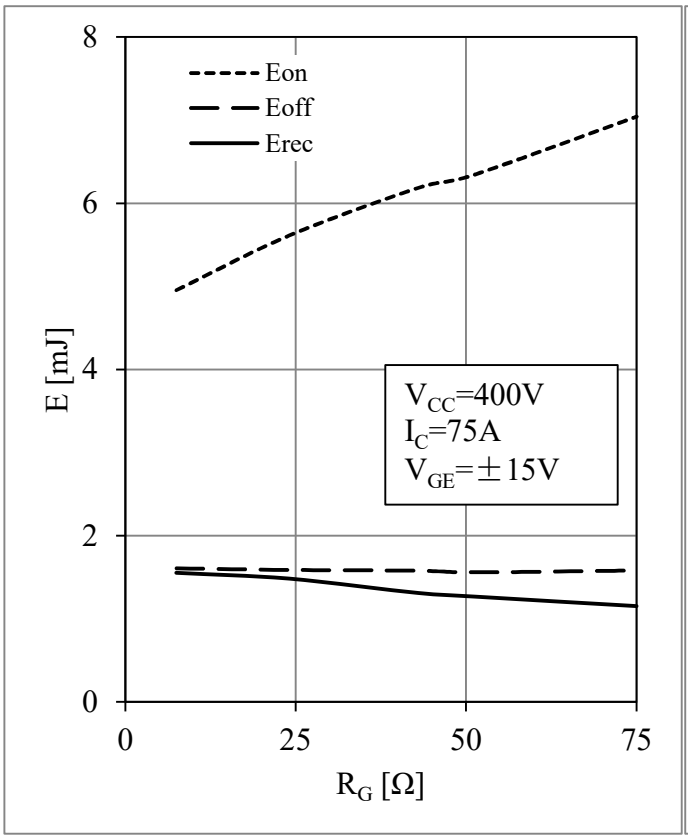


Fig 11. Switching Energy Loss vs. R_G

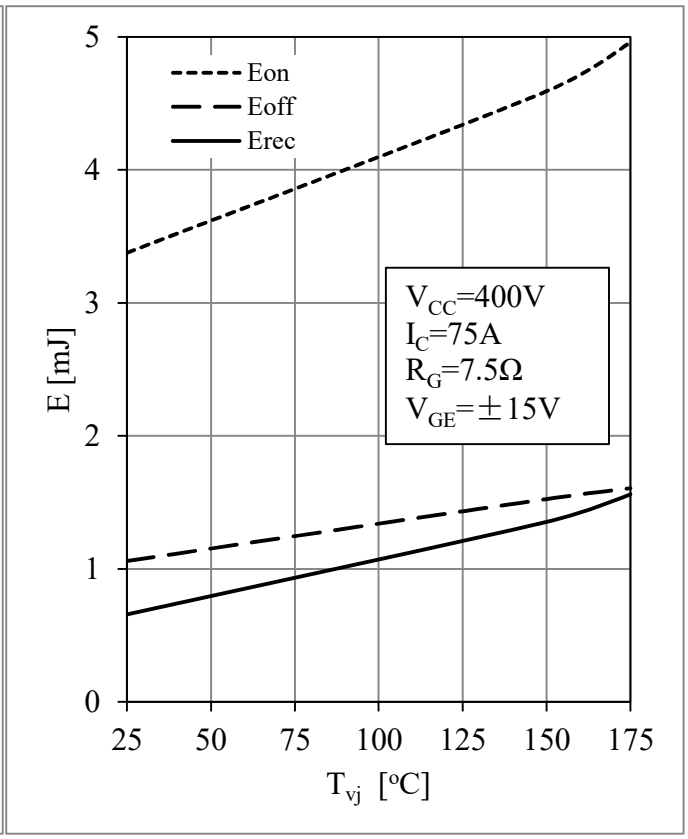


Fig 12. Switching Energy Loss vs. T_{vj}

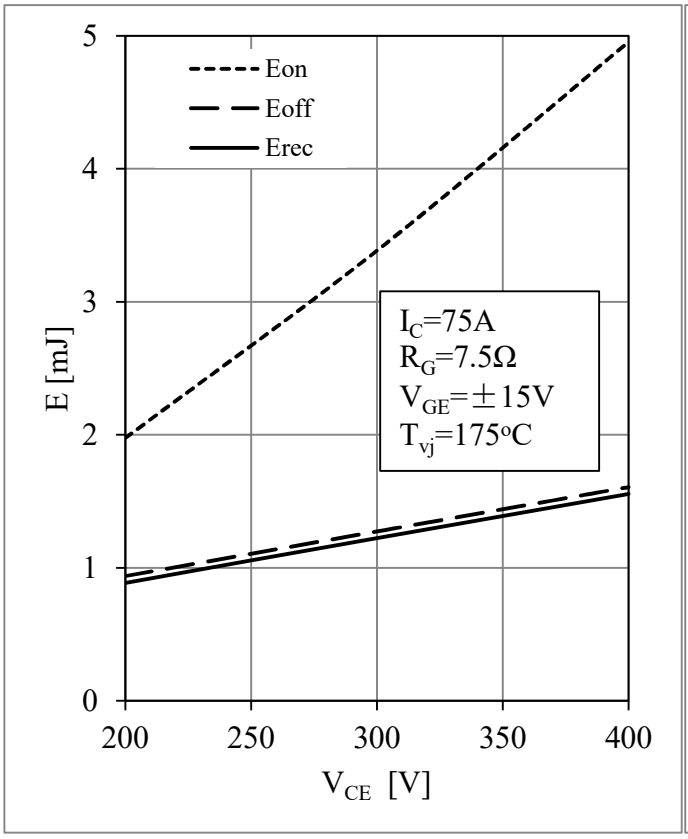


Fig 13. Switching Energy Loss vs.V_{CE}

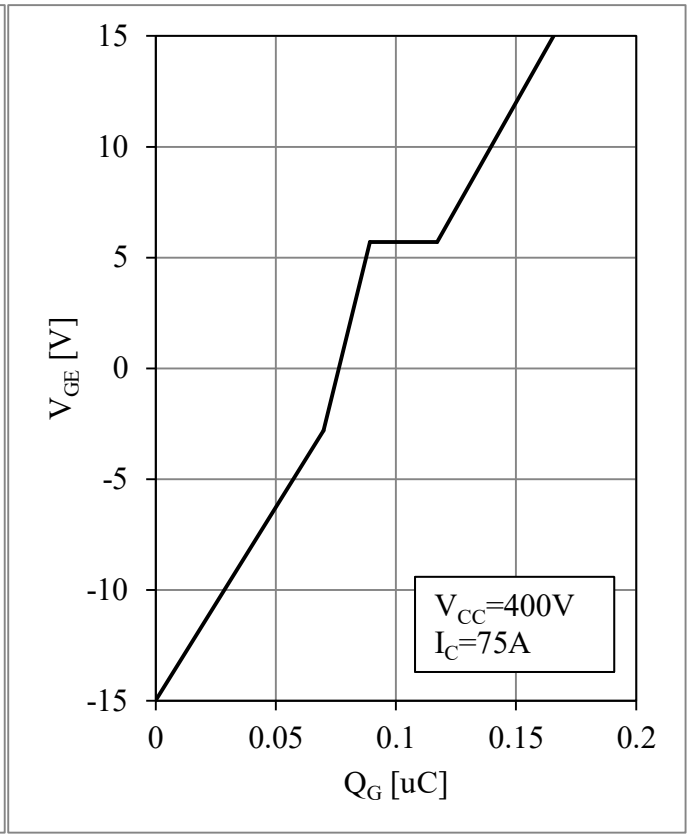


Fig 14. IGBT Gate Charge Characteristic

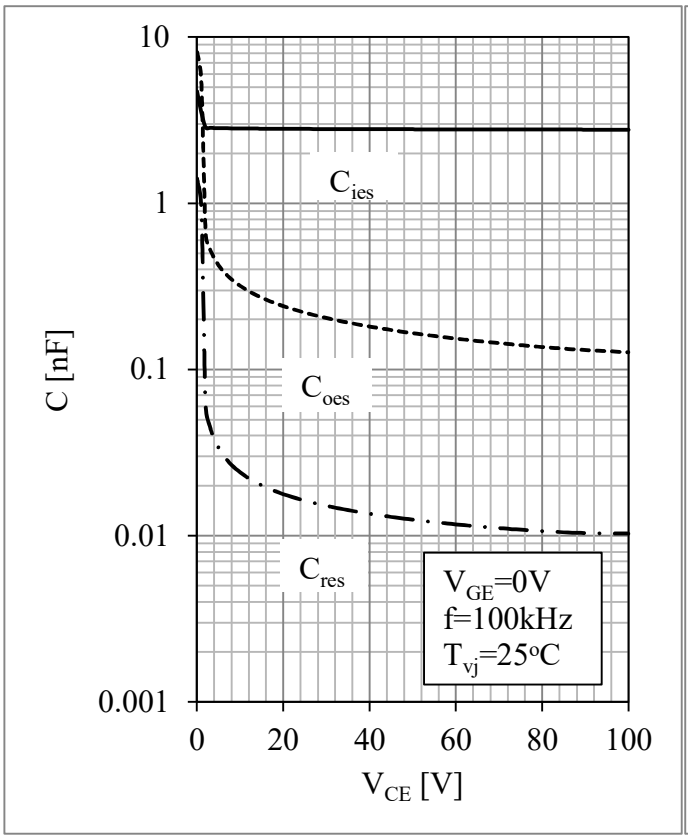


Fig 15. IGBT Capacity Charcteristic

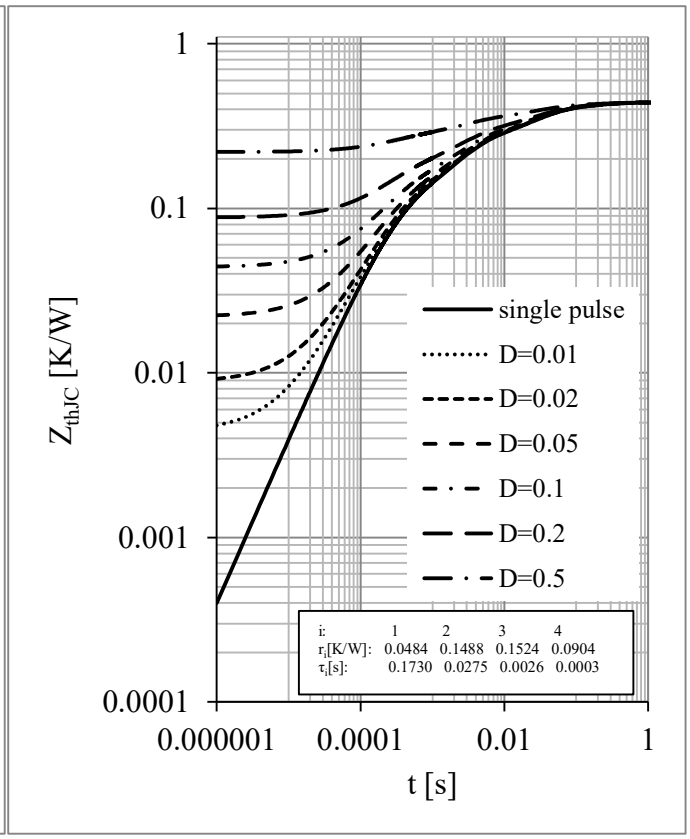


Fig 16. IGBT Transient Thermal Impedance

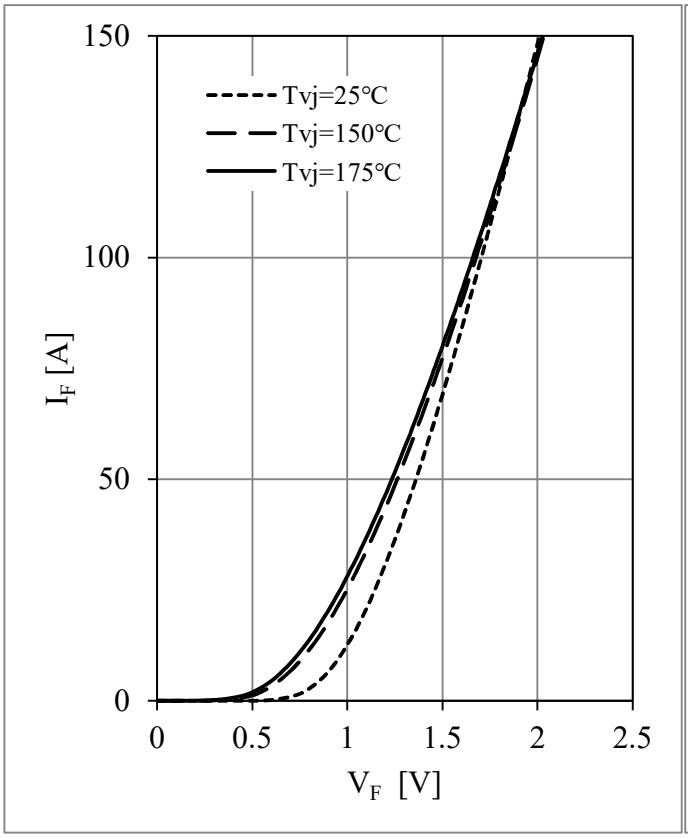


Fig 17. Diode Forward Characteristics

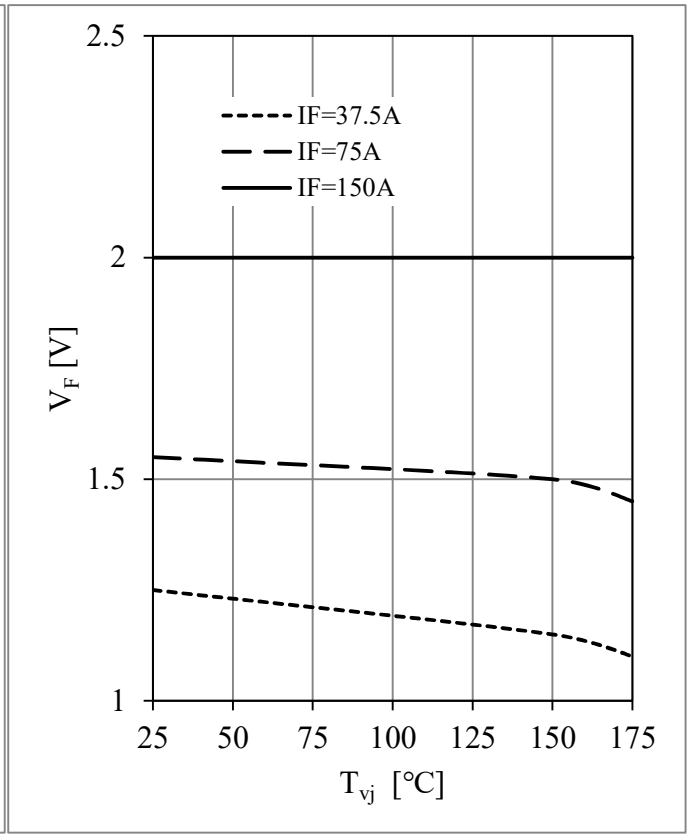


Fig 18. Diode Forward Voltage Vs T_{vj}

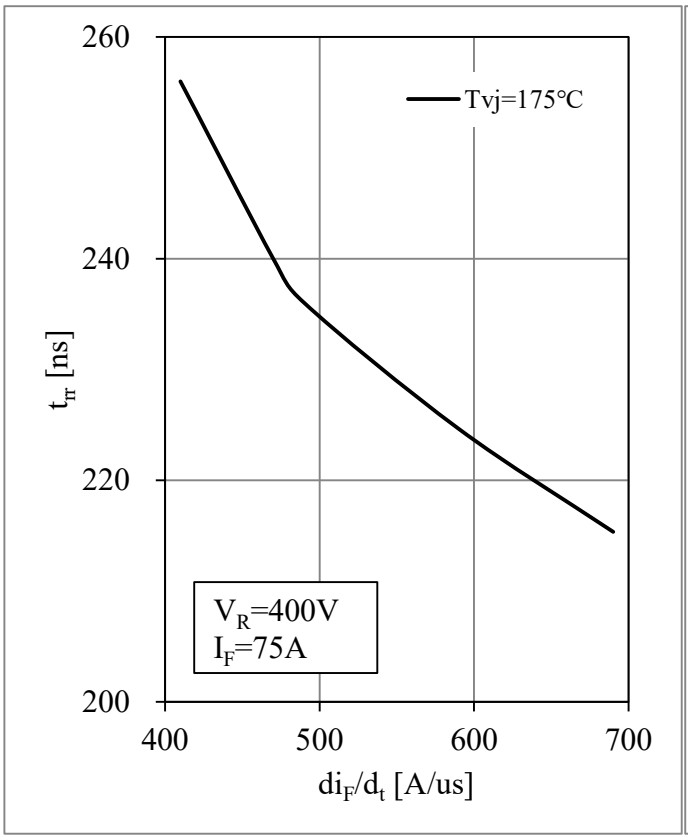


Fig 19. Reverse Recovery Time vs. diF/dt

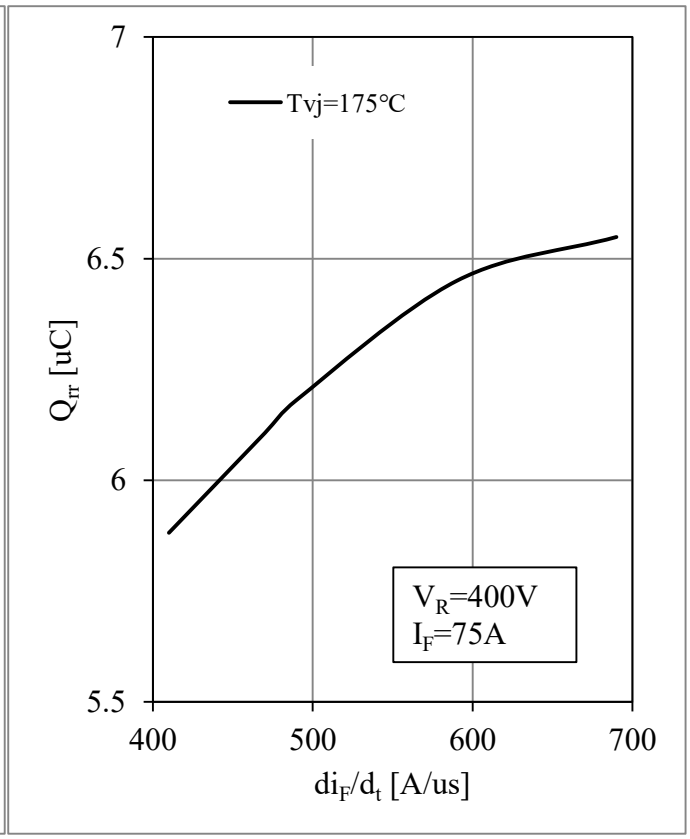


Fig 20. Reverse Recovery Charge vs. diF/dt

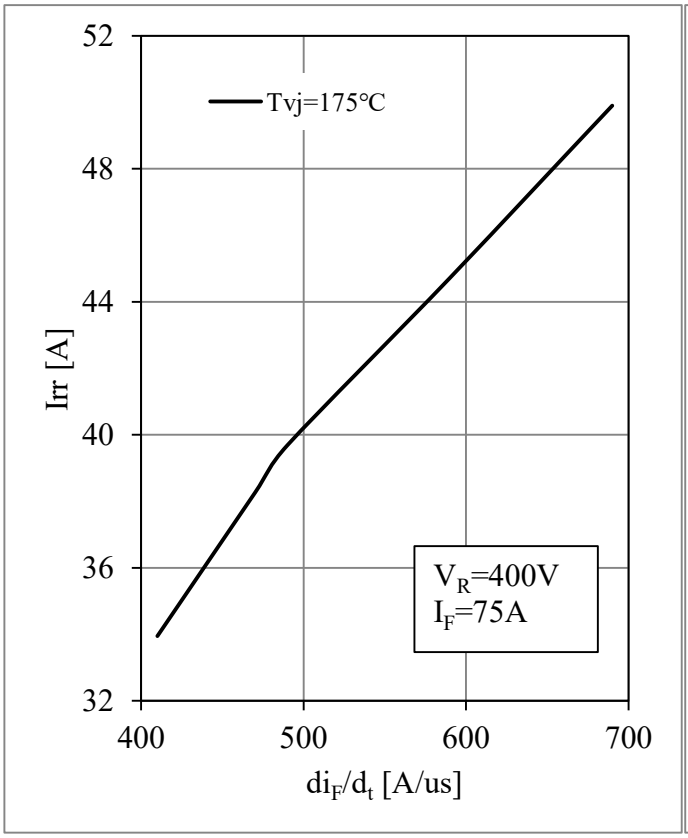


Fig 21. Reverse Recovery Current vs. di_F/d_t

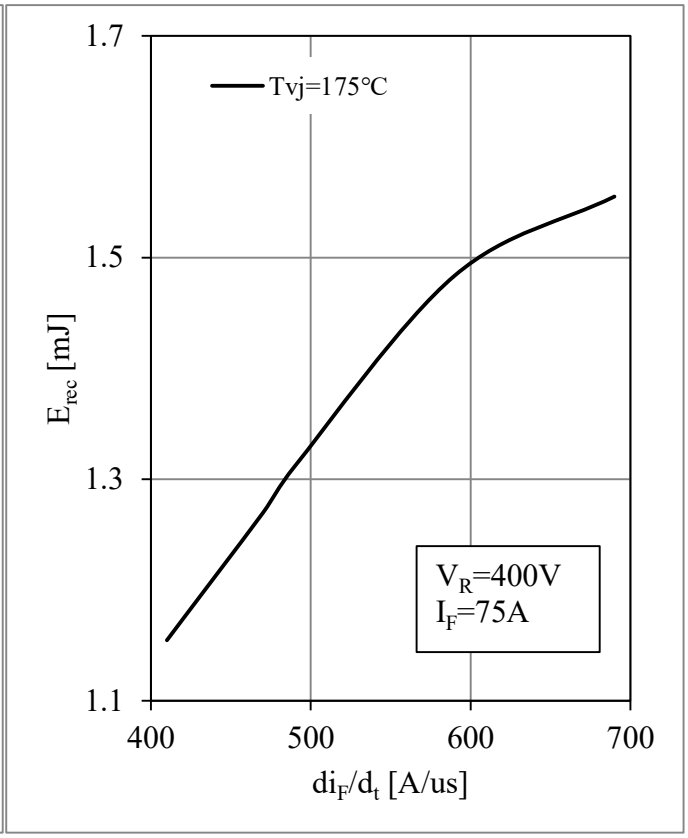


Fig 22. Reverse Energy Losses vs. diF/dt

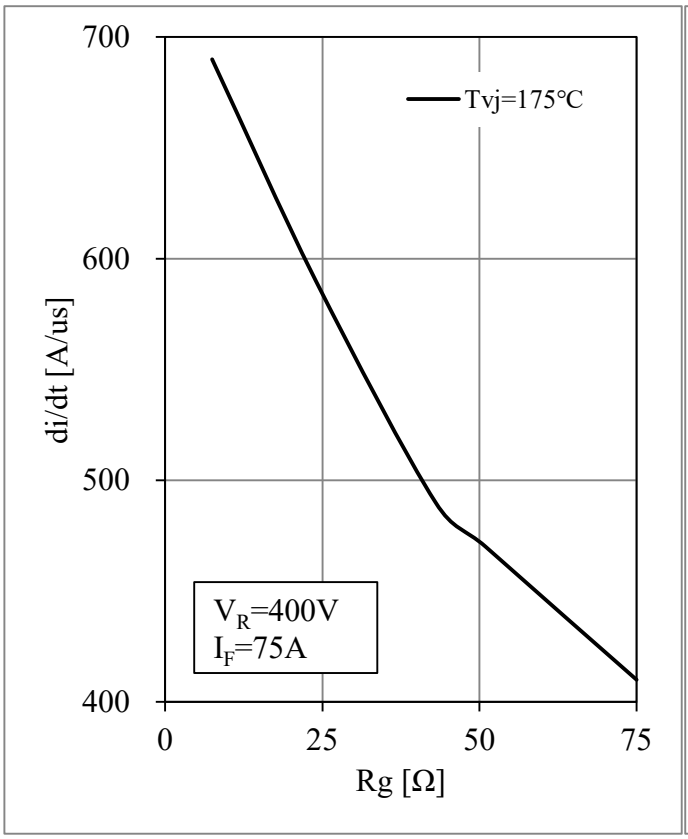


Fig 23. diF/dt vs Rg

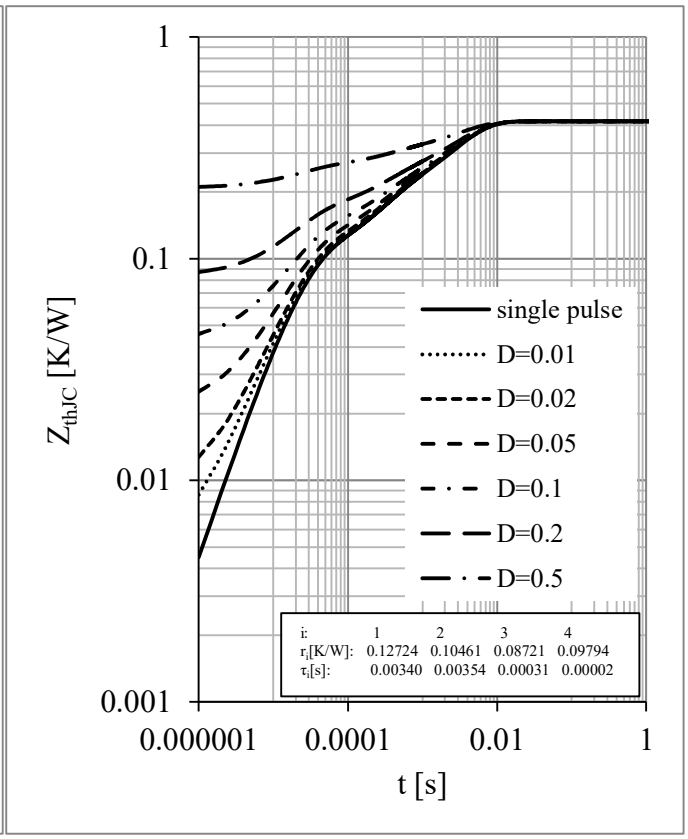
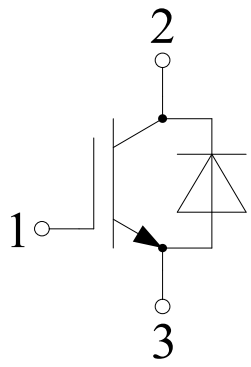


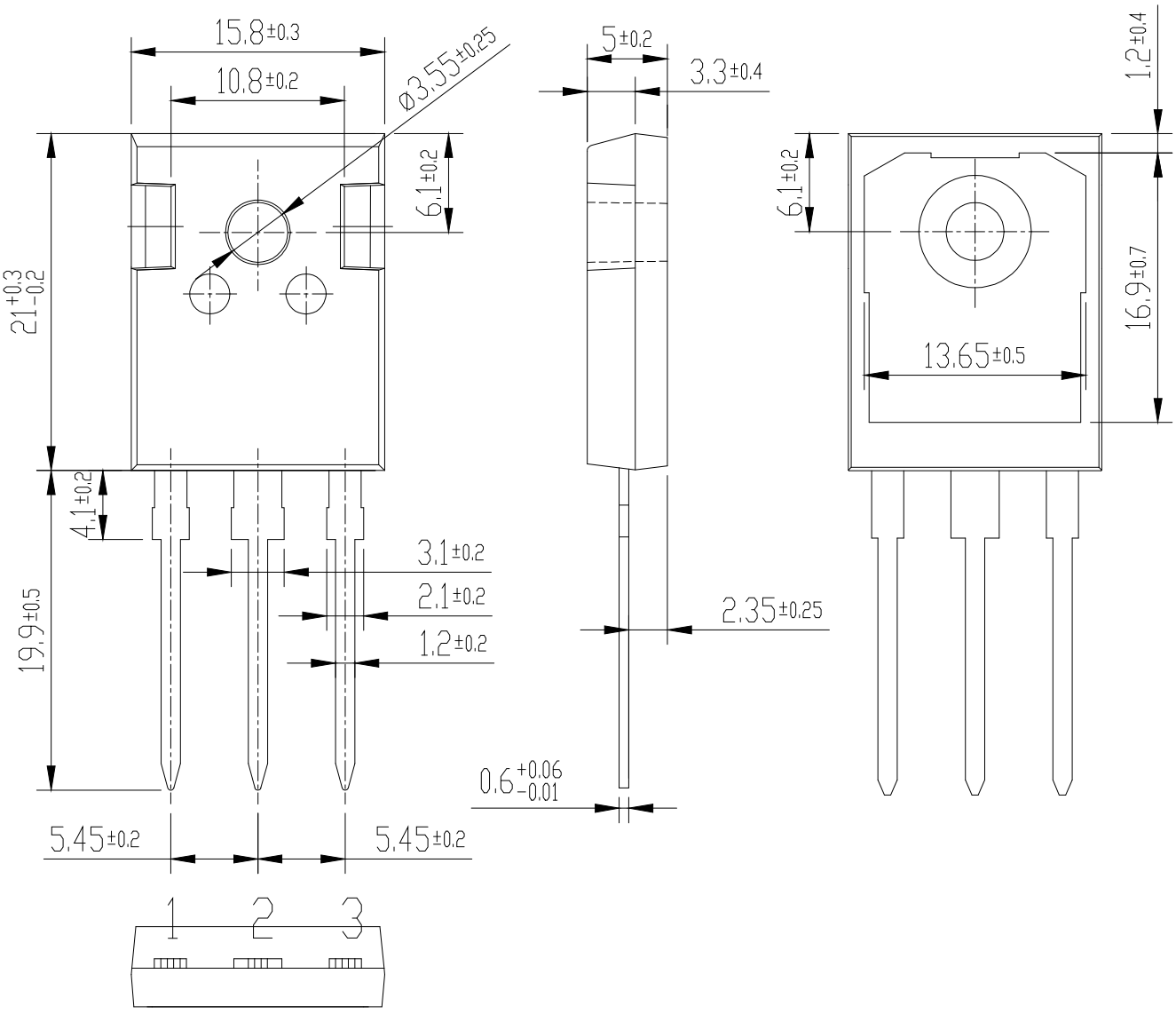
Fig 24. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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